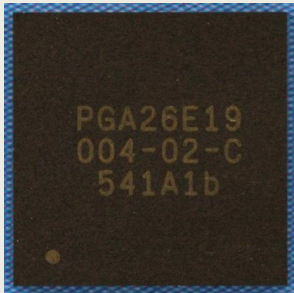


PANASONIC PGA26E19BA GaN POWER HEMT ANALYSIS REPORT

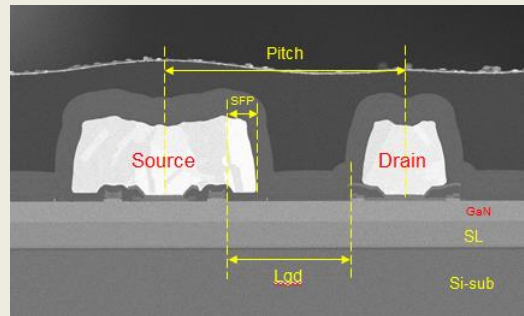
June 20, 2016. This is a detailed structure and process analysis report of the PGA26E19BA GaN POWER HEMT offered in DFN package



DFN package.



Die image



Die cross-section

Both of these products are part of Panasonic's X-GaN™ family, one of the most promising normally OFF GaN HEMT manufacturing processes currently available. Currently only Panasonic and GaN Systems Inc offers normally off lateral HEMT products in the 600V application regime. Panasonic's X-GaN™ technology succeeded in eliminating the troublesome "current collapse" phenomenon, a major reliability concern traditionally associated with GaN technology.

This analysis report reveals the details of (1) the normally-off recessed P-GaN channel, (2) high voltage layout, (3) drain P-GaN structure for suppressing "current collapse", (4) gate ESD protection structure and (5) mask/process sequence.

Given the considerable interest in GaN™ technology, LTEC Corporation offers a detailed construction analysis report for not only the PGA26E19BA, but also for the PGA26C09DV. In addition, similar reports are available for GaN Systems' GS66508P device. Refer to the table of contents for additional details.

Note:

The listed report price may not be accurate as it decreases over time.

Please contact us for current report pricing info@ltecusa.com

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